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## Abstract of the Disclosure

In a semiconductor laser device, an AlGa<sub>N</sub> buffer layer, a Ga<sub>N</sub> layer, an n-Ga<sub>N</sub> layer, an n-AlGa<sub>N</sub> cladding layer, an MQW light emitting layer, a p-AlGa<sub>N</sub> cladding layer, a p-first Ga<sub>N</sub> cap layer, a current blocking layer composed of n-AlGa<sub>N</sub>, and a p-second Ga<sub>N</sub> cap layer are stacked in this order on a sapphire substrate, and a ridge portion having an upper surface having a width  $W_1$  is formed by etching. The current blocking layer has an opening having a width  $W_2$  on the upper surface of the ridge portion. The width  $W_2$  of the opening is smaller than the width  $W_1$  of the upper surface of the ridge portion. Accordingly, in a light emitting region of the MQW light emitting layer, a saturable light absorbing region is formed on both sides of a current injection region.